

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : H. OHTANI
Serial No.: 08/730,038
Filed : 5/23/97
Title : SEMICONDUCTOR INTEGRATED CIRCUIT AND FABRICATING METHOD
THEREOF

Art Unit:
Examiner:

Assistant Commissioner for Patents
Washington, DC 20231

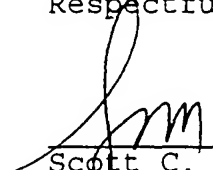
TRANSMITTAL OF PRIORITY DOCUMENT(S) UNDER 35 U.S.C. 119

Applicant hereby confirms his claim of priority under 35 U.S.C. 119 from Japanese Application No. 8-165272 filed June 4, 1996. A certified copy of the application from which priority is claimed is submitted herewith.

Please charge any fees due in this respect to Deposit Account No. 06-1050..

Respectfully submitted,

Date: 2/15/97



Scott C. Harris
Reg. No. 32,030

Fish & Richardson P.C.
4225 Executive Square, Suite 1400
La Jolla, CA 92037

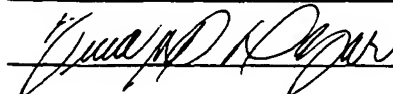
Telephone: 619/678-5070
Facsimile: 619/678-5099

36106.LJ1

Date of Deposit 7-16-97

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated above and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

YINIA M. NAJAR



Yinia M. Najjar

日 本 国 特 許 庁

PATENT OFFICE
JAPANESE GOVERNMENT

別紙添付の書類に記載されている事項は下記の出願書類に記載されて
る事項と同一であることを証明する。

This is to certify that the annexed is a true copy of the following application as filed
in this Office.

出 願 年 月 日

Date of Application:

1996年 6月 4日

出 願 番 号

Application Number:

平成 8年特許願第165272号

出 願 人

Applicant(s):

株式会社半導体エネルギー研究所

1997年 5月16日

特 許 庁 長 官
Commissioner,
Patent Office

荒井寿光



出証番号 出証特平09-3035926